

## LIST OF CLAIMS

Claims 1 through 3 – CANCELLED

Claim 4. (ORIGINAL) A method of dielectric layer formation, comprising the steps of:

- (a) plasma-enhanced depositing a first sublayer on a substrate with a plasma-to-substrate bias of less than a first threshold voltage; and
- (b) plasma-enhanced depositing a second sublayer on a substrate with a plasma-to-substrate do bias of greater than a second threshold voltage with said second threshold voltage greater than said first threshold voltage.

Claim 5. (ORIGINAL) The method of claim 4, wherein:

- (a) said first threshold voltage is less than about 150 volts; and
- (b) said second threshold voltage is greater than about 300 volts.

Claim 6. (ORIGINAL) The method of claim 4, wherein:

- (a) said first and second sublayers are silicon oxides with at least one of said first and second sublayers including dopants.

Claim 7. (ORIGINAL) A method of premetal dielectric fabrication for an integrated circuit, comprising the steps of:

- (a) providing a substrate with insulated gate structures at a first surface; and
- (b) plasma-enhanced depositing a dielectric layer over said gates and substrate with a plasma-to-substrate bias initially less than a first threshold voltage but increasing to greater than a second threshold voltage which exceeds said first threshold voltage;
- (c) wherein said first threshold voltage is characterized by conformal deposition and said second threshold voltage is characterized by planarizing deposition.

Claim 8. (ORIGINAL) The method of claim 7, wherein:

(a) said dielectric layer is made of silicon oxides.

Claim 9. (ORIGINAL) The method of claim 8, wherein:

(a) said silicon oxides include dopants in at least a portion remote from said gate structures and substrate.

Claim 10. (ORIGINAL) The method of claim 8, wherein:

(a) said silicon oxides include dopants in at least a portion adjacent said gate structures and substrate.